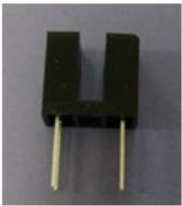


ITR8105



Features

- Cut-off visible wavelength $\lambda_p=940\text{nm}$
- Fast response time
- High sensitivity
- Pb free
- This product itself will remain within RoHS compliant version

Description

The **ITR8105** consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR only. This is the normal situation. But when an object is in between, phototransistor could not receive the radiation.

Applications

- Mouse Copier
- Switch Scanner
- Floppy disk driver
- Non-contact Switching
- For Direct Board

Device Selection Guide

Device No.	Chip Material	LENS COLOR
IR	GaAlAs	Water Clear
PT	Silicon	Water Clear

Absolute Maximum Ratings (Ta=25 °C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25 °C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V _R	5	V
	Forward Current	I _F	50	mA
	Peak Forward Current (*1) Pulse width 100 μs, Duty cycle=1%	I _{FP}	1	A
Output	Collector Power Dissipation	P _C	75	mW
	Collector Current	I _C	20	mA
	Collector-Emitter Voltage	B V _{CEO}	30	V
	Emitter-Collector Voltage	B V _{ECO}	5	V
Operating Temperature		Topr	-25~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	

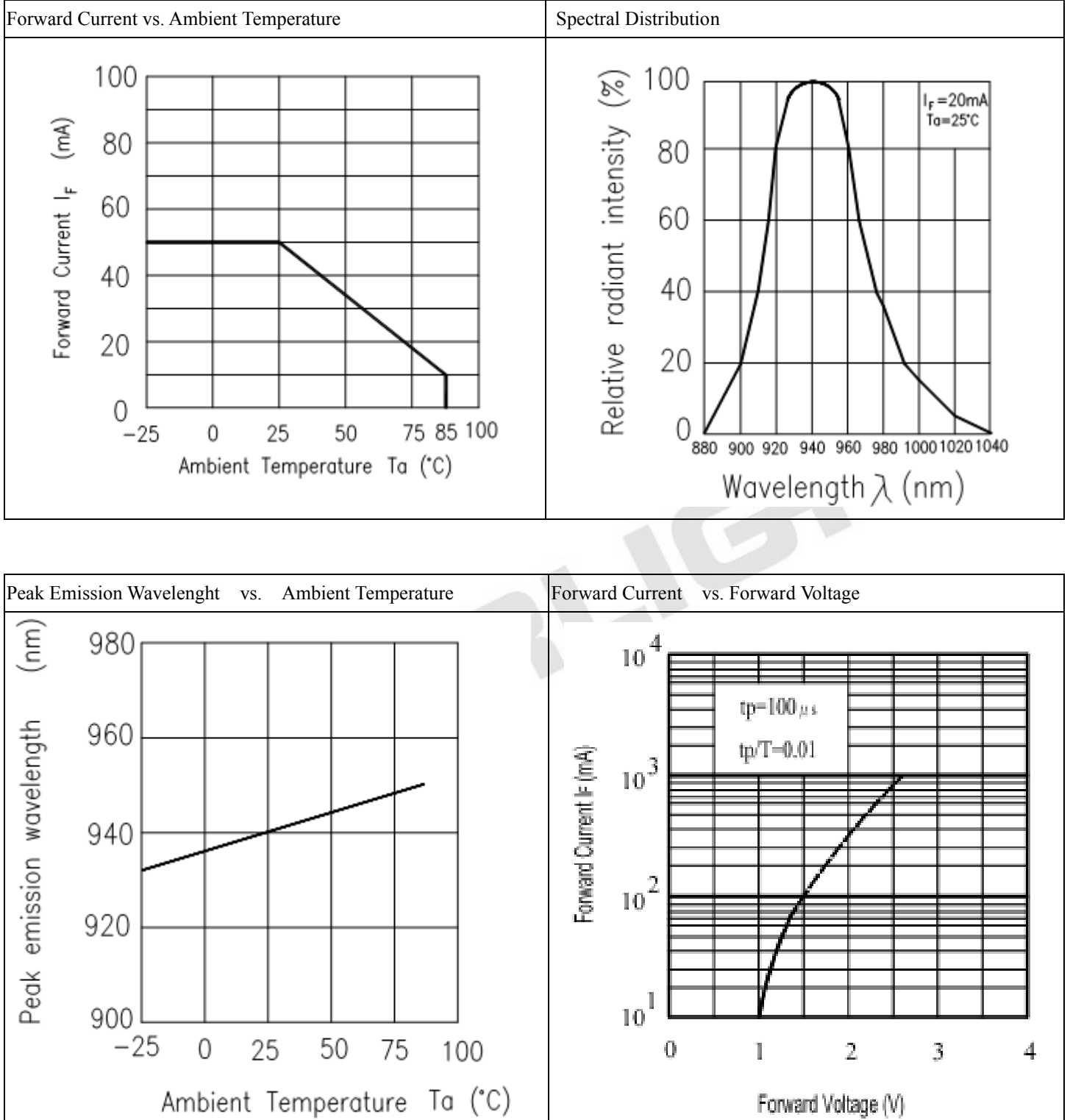
(* 1) $t_w=100 \mu \text{ sec.}$, $T=10 \text{ msec.}$ (* 2) $t=5 \text{ Sec}$

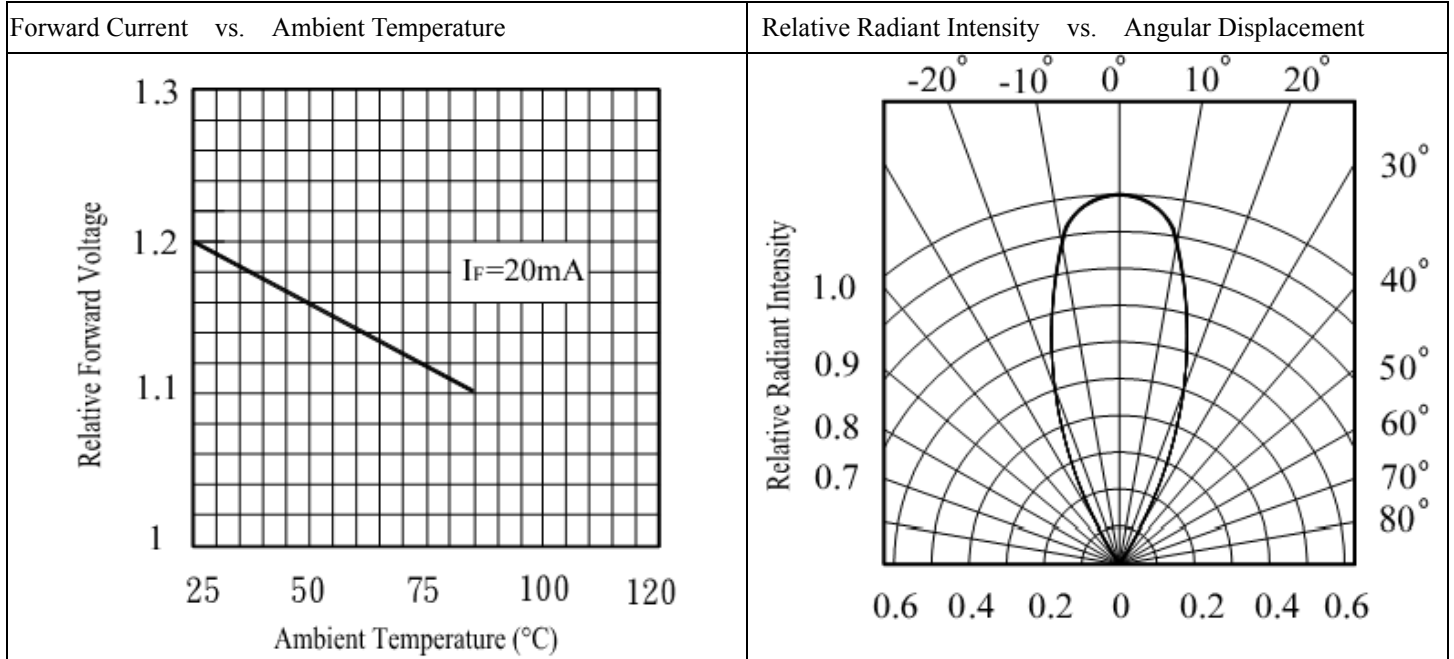
Electro-Optical Characteristics (Ta=25)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward Voltage	V_F	---	1.2	1.6	V	$I_F=20\text{mA}$
	Reverse Current	I_R	---	---	10	μA	$V_R=5\text{V}$
	Peak Wavelength	λ_p	---	940	---	nm	$I_F=20\text{mA}$
	View Angle	2 θ 1/2	---	40	---	Deg	$I_F=20\text{mA}$
Output	Dark Current	I_{CEO}	---	---	100	nA	$V_{CE}=20\text{V}, E_e=0\text{mW/cm}^2$
	C-E Saturation Voltage	$V_{CE(sat)}$	---	---	0.4	V	$I_C=2\text{mA}$ $E_e=1\text{mW/cm}^2$
Transfer Characteristics	Collect Current	$I_C(ON)$	0.9	---	15	mA	$V_{CE}=5\text{V } I_F=20\text{mA}$
	Rise time	t_r	---	15	---	μsec	$V_{CE}=5\text{V}$ $I_C=1\text{mA}$
	Fall time	t_f	---	15	---	μsec	$R_L=1\text{K}\Omega$

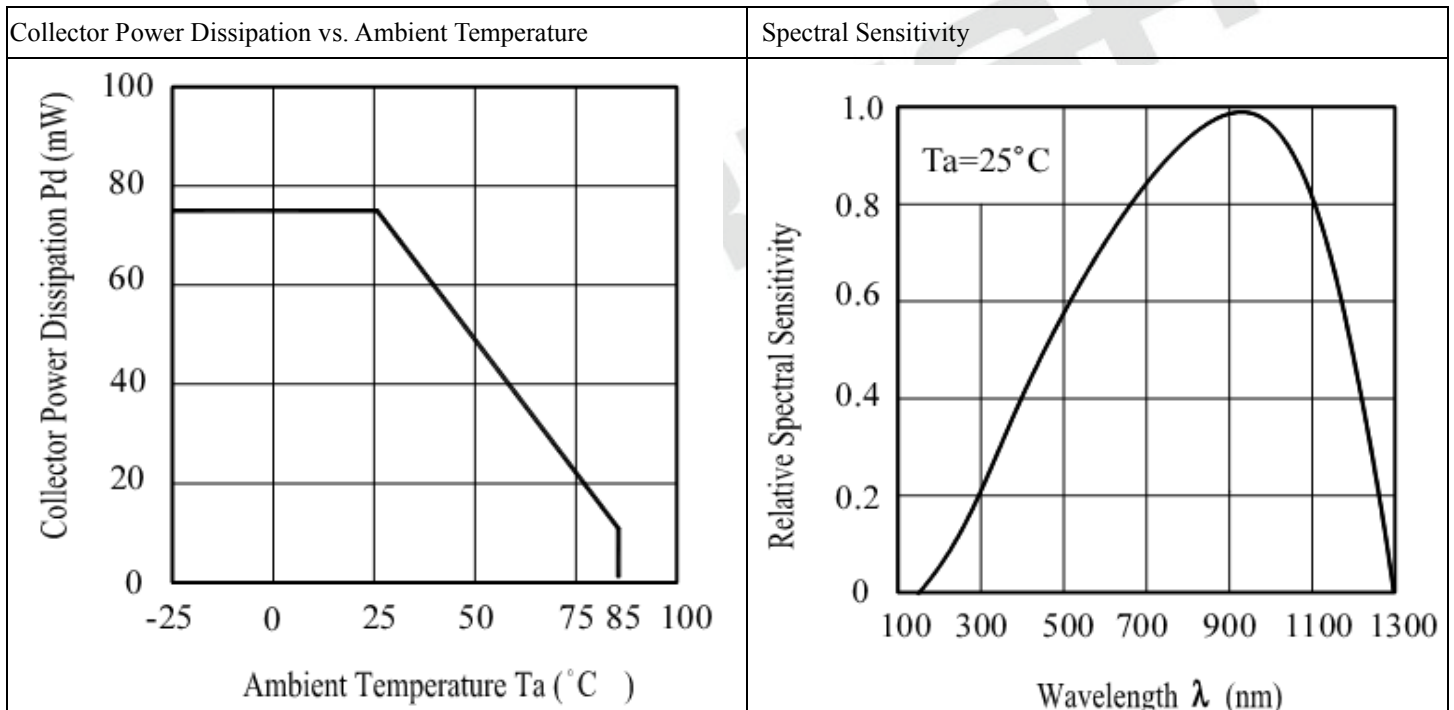
EVERLIGHT

Typical Electrical/Optical/Characteristics Curves for IR

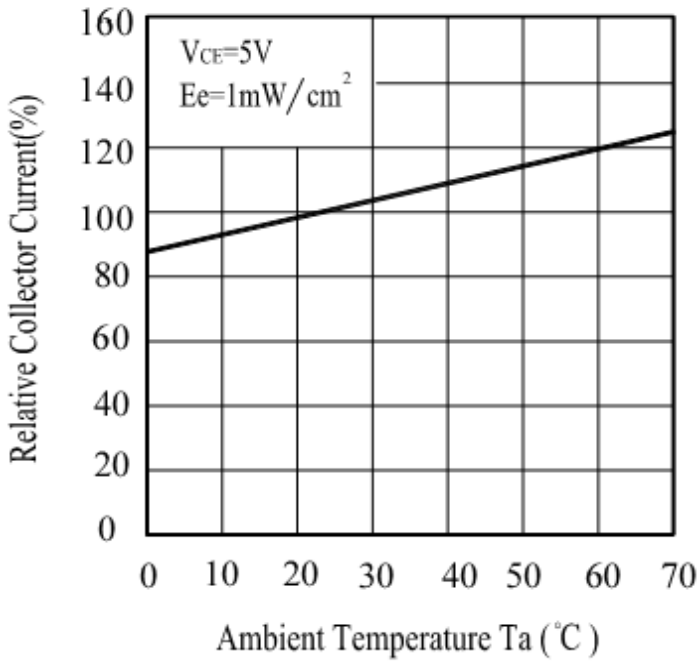




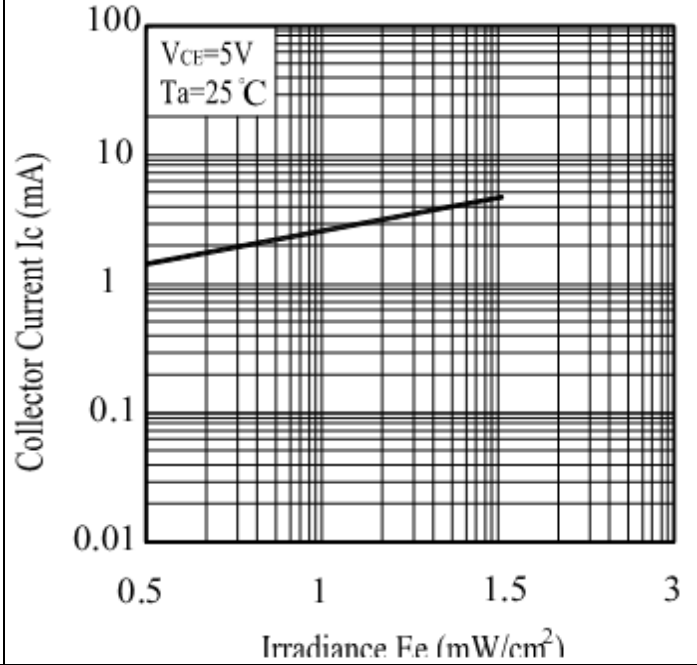
Typical Electro/Optical/Characteristics Curves for PT



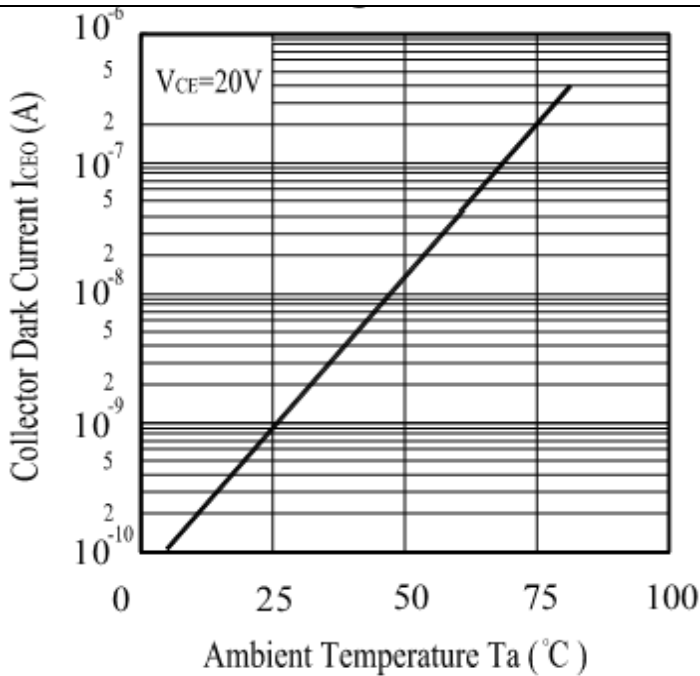
Relative Collector Current vs Ambient Temperature



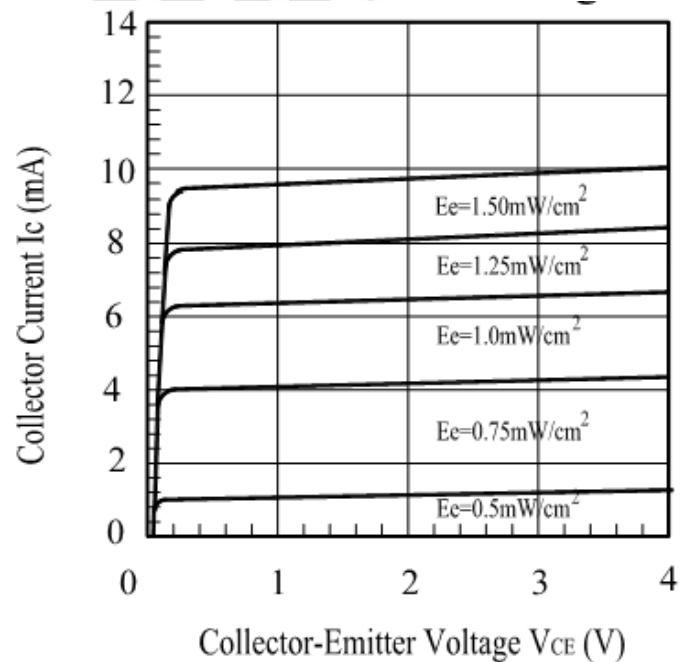
Collector Current vs. Irradiance



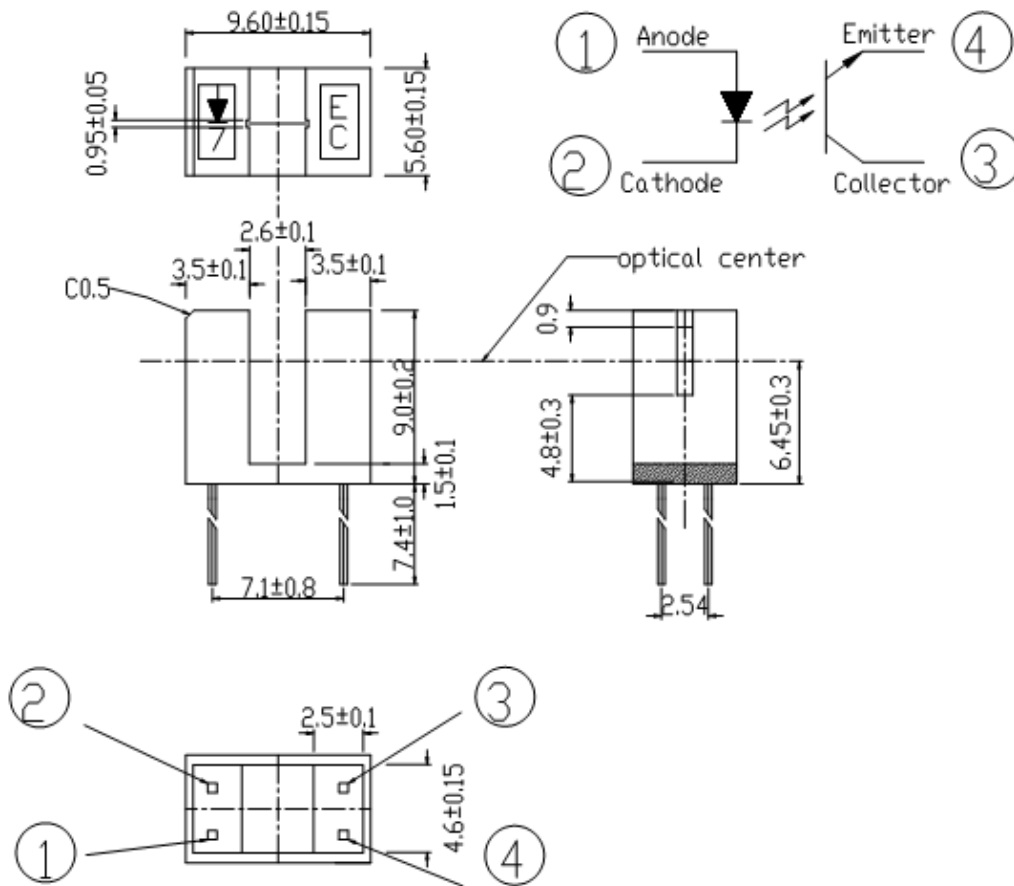
Collector Current vs. Ambient Temperature



Collector Current vs. Collector-emitter Voltage



Package Dimension



Notes:

1. All dimensions are in millimeters
2. Tolerances unless dimensions ± 0.2 mm
3. Lead spacing is measured where the lead emerge from the package
4. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification
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